

SN74AHC240-Q1 Automotive Octal Buffers/Drivers With 3-State Outputs

1 Features

- AEC-Q100 qualified for automotive applications:
 - Device temperature grade 1: -40°C to +125°C
 - Device HBM ESD classification level 2
 - Device CDM ESD classification level C4B
- Operating range 2V to 5.5V V_{CC}
- Low delay, 6ns typ (25°C, 5V)
- Latch-up performance exceeds 250mA per JESD 17

2 Applications

- Handset: smartphone
- **Network switch**
- Health fitness and wearables

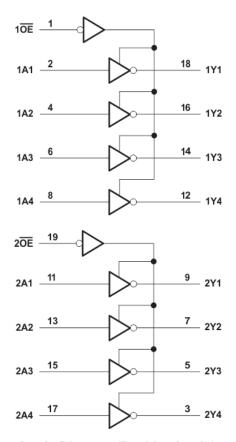
3 Description

These octal buffers/drivers are designed specifically to improve the performance and density of 3-state memory-address drivers, clock drivers, and busoriented receivers and transmitters.

Package Information

PART NUMBER	PACKAGE ⁽¹⁾	PACKAGE SIZE(2)	BODY SIZE (NOM)(3)
SN74AHC240-Q1	PW (TSSOP, 20)	6.5mm × 6.4mm	6.5mm × 4.4mm

- For more information, see Section 11.
- The package size (length × width) is a nominal value and (2)includes pins, where applicable.
- The body size (length × width) is a nominal value and does not include pins..



Logic Diagram (Positive Logic)



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4 Pin Configuration and Functions

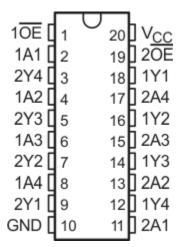


Figure 4-1. SN74AHC240-Q1 PW Package (Top View)

F	PIN	- TYPE ⁽¹⁾	DESCRIPTION
NAME	NO.	ITPE	DESCRIPTION
10E	1	0	Output enable 1
1A1	2	I	1A1 input
2Y4	3	0	2Y4 output
1A2	4	I	1A2 input
2Y3	5	0	2Y3 output
1A3	6	I	1A3 input
2Y2	7	0	2Y2 output
1A4	8	I	1A4 input
2Y1	9	0	2Y1 output
GND	10	G	Ground pin
2A1	11	I	2A1 input
1Y4	12	0	1Y4 output
2A2	13	I	2A2 input
1Y3	14	0	1Y3 output
2A3	15	I	2A3 input
1Y2	16	0	1Y2 output
2A4	17	I	2A4 input
1Y1	18	0	1Y1 output
20E	19	0	Output enable 2
VCC	20	Р	Power pin

⁽¹⁾ Signal Types: I = Input, O = Output, I/O = Input or Output



5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V _{CC}	Supply voltage range	Supply voltage range			
Vı	Input voltage range ⁽²⁾		-0.5	7	V
Vo	Voltage range applied to any outp	ut in the high-impedance or power-off state ⁽²⁾	-0.5	7	V
Vo	Output voltage range ⁽²⁾		-0.5	V _{CC} + 0.5	V
I _{IK}	Input clamp current	V _I < -0.5V		-20	mA
I _{OK}	Output clamp current	V_{O} < -0.5V or V_{O} > V_{CC+} 0.5V		±20	mA
Io	Continuous output current	$V_O = 0$ to V_{CC}		±25	mA
	Continuous output current through	N V _{CC} or GND		±75	mA
T _{stg}	Storage temperature		-65	150	°C

⁽¹⁾ Operation outside the Absolute Maximum Ratings may cause permanent device damage. Absolute maximum ratings do not imply functional operation of the device at these or any other conditions beyond those listed under Recommended Operating Conditions. If briefly operating outside the Recommended Operating Conditions but within the Absolute Maximum Ratings, the device may not sustain damage, but it may not be fully functional. Operating the device in this manner may affect device reliability, functionality, performance, and shorten the device lifetime.

5.2 ESD Ratings

			VALUE	UNIT
	Electrostatic	Human body model (HBM), per AEC Q100-002 HBM ESD Classification Level 2 ⁽¹⁾	±2000	
V _(ESD)	discharge	Charged device model (CDM), per AEC Q100-011 CDM ESD Classification Level C4B	±1000	V

⁽¹⁾ AEC Q100-002 indicate that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

5.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

Specification	Description	Condition	MIN	MAX	UNIT
V _{CC}	Supply voltage		2	5.5	V
		V _{CC} = 2V	1.5		
V _{IH}	High-level input voltage	V _{CC} = 3V	2.1		V
		V _{CC} = 5.5V	3.85		
	Low-Level input voltage	V _{CC} = 2V		0.5	
V _{IL}	Low-Level input voltage	V _{CC} = 3V		0.9	V
	Low-Level input voltage	V _{CC} = 5.5V		1.65	
V _I	Input Voltage		0	5.5	V
Vo	Output Voltage		0	V _{CC}	V
		V _{CC} = 2V		-50	μΑ
I _{OH}	High-level output current	V _{CC} = 3.3V ± 0.3V		-4	mA
		V _{CC} = 5V ± 0.5V		-8	mA
		V _{CC} = 2V		50	μΑ
I _{OL}	Low-level output current	V _{CC} = 3.3V ± 0.3V		4	mA
		V _{CC} = 5V ± 0.5V		8	mA
44/4	Inner the transplation wise on fall mate	$V_{CC} = 3.3V \pm 0.3V$		100	ns/V
Δt/Δv	Input transition rise or fall rate	$V_{CC} = 5V \pm 0.5V$		20	ns/V
T _A	Operating free-air temperature		-40	125	°C

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⁽²⁾ The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

5.4 Thermal Information

	THERMAL METRIC ⁽¹⁾	PW (TSSOP)	UNIT
	I DERIVIAL METRIC	20 PINS	UNIT
R _{0JA}	Junction-to-ambient thermal resistance	116.8	°C/W
R _{0JC(top)}	Junction-to-case (top) thermal resistance	58.5	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	78.7	°C/W
ΨЈТ	Junction-to-top characterization parameter	12.6	°C/W
ΨЈВ	Junction-to-board characterization parameter	77.9	°C/W
R _{0JC(bot)}	Junction-to-case (bottom) thermal resistance	N/A	°C/W

⁽¹⁾ For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

5.5 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V	T _A :	= 25°C		-40°C	UNIT		
PARAMETER	TEST CONDITIONS	V _{cc}	MIN	TYP	MAX	MIN	TYP	MAX	UNII
	I _{OH} = -50μA	2V to 5.5V	V _{CC} -0.1	V _{CC}		V _{CC} -0.1	V _{CC}		
V _{OH}	I _{OH} = -4mA	3V	2.58			2.48			V
	I _{OH} = −8mA	4.5V	3.94			3.8			
	I _{OL} = 50μA	2V to 5.5V			0.1			0.1	
V _{OL}	I _{OL} = 4mA	3V			0.36			0.44	V
	I _{OL} = 8mA	4.5V			0.36			0.44	
II	V_I = 5.5V or GND and V_{CC} = 0V to 5.5V	0V to 5.5V			±0.1			±1	μA
loz	$V_O = V_{CC}$ or GND and V_{CC} = 5.5V	5.5V			±0.25			±5	μA
Icc	$V_I = V_{CC}$ or GND, $I_O = 0$, and $V_{CC} = 5.5V$	5.5V			4			40	μA
C _I	V _I = V _{CC} or GND	5V		2	10			10	pF
Co	Vo = V _{CC} or GND	5V		5					pF
C _{PD}	No load, F = 1MHz	5V		15					pF

5.6 Switching Characteristics

 C_L = 50pF; over operating free-air temperature range; typical values measured at T_A = 25°C (unless otherwise noted). See *Parameter Measurement Information*

PARAMETER	FROM	то	LOAD	V _{CC}	TA	= 25°C		-40°C	to 125°	С	UNIT
TANAMETER	(INPUT)	(OUTPUT)	CAPACITANCE	V CC	MIN	TYP	MAX	MIN	TYP	MAX	UNII
t _{PLH}	A	Υ	C ₁ = 15pF	2V			19.5	1		23	ns
t _{PHL}		I	С[- 13рг	2 V			19.5	1		23	ns
t _{PZH}	- OE	Υ					25.5	1		30	ns
t _{PZL}	OL		C _L = 15pF				25.5	1		30	ns
t _{PHZ}	- ŌĒ	Υ	C _L = 15pF	2V			25.5	1		30	ns
t _{PLZ}	OL	I					25.5	1		30	ns
t _{PLH}	A	Υ	C = 15pE	3.3V		5.3	7.5	1		9	ns
t _{PHL}		Y	C _L = 15pF	ΣL = 13μr 3.3V -		5.3	7.5	1		9	ns
t _{PZH}	- ŌE	V	C. = 15pE	3.3V		6.6	10.6	1		12.5	ns
t _{PZL}	ŌĒ Y	I	$Y \qquad C_{L} = 15pF \qquad 3.3V$		6.6	10.6	1		12.5	ns	



5.6 Switching Characteristics (continued)

 C_L = 50pF; over operating free-air temperature range; typical values measured at T_A = 25°C (unless otherwise noted). See *Parameter Measurement Information*

DADAMETED	FROM		LOAD	V	T _A	= 25°C		-40°0	C to 125°C	UNIT
PARAMETER	(INPUT)	(OUTPUT)	CAPACITANCE	V _{CC}	MIN	TYP	MAX	MIN	TYP MAX	UNII
t _{PHZ}	ŌĒ	Υ	C = 15pF	2 2)/		7.8	11.5	1	12.5	ns
t _{PLZ}		Ţ	C _L = 15pF	3.3V		7.8	11.5	1	12.5	ns
t _{PLH}	^	Υ	C _L = 15pF	5V		3.6	5.5	1	6.5	ns
t _{PHL}	A	Ţ	CL = 15pr	30		3.6	5.5	1	6.5	ns
t _{PZH}	ŌĒ	Υ	C = 15pE	5V		4.7	7.3	1	8.5	ns
t _{PZL}	- OE	Ţ	$C_L = 15pF$	30		4.7	7.3	1	8.5	ns
t _{PHZ}	ŌĒ	Υ	C = 15pF	5V		5.2	7.2	1	8.5	ns
t _{PLZ}	JOE	Y	C _L = 15pF	ον		5.2	7.2	1	8.5	ns
t _{PLH}	_	V	C - 50=5	2)./			26.5	1	30	ns
t _{PHL}	A	Y	C _L = 50pF	2V			26.5	1	30	ns
t _{PZH}	ŌĒ	V	C - 50=5	2)./			32.5	1	36.5	ns
t _{PZL}	JOE	Υ	C _L = 50pF	2V			32.5	1	36.5	ns
t _{PHZ}	ŌĒ	V	C - 50=5	2)./			32	1	36.5	ns
t _{PLZ}	OE	Υ	C _L = 50pF	2V			32	1	36.5	ns
t _{PLH}	^	Υ	C = 50pF	3.3V		7.8	11	1	12.5	ns
t _{PHL}	- A	Ť	$C_L = 50pF$	3.30		7.8	11	1	12.5	ns
t _{PZH}	ŌĒ	V	C - 50-5	2.21/		9.1	14.1	1	16	ns
t _{PZL}	JOE	Y	C _L = 50pF	3.3V		9.1	14.1	1	16	ns
t _{PHZ}	ŌĒ	V	C - 50=5	2.21/		10.3	14	1	16	ns
t _{PLZ}	OE	Y	C _L = 50pF	3.3V		10.3	14	1	16	ns
t _{PLH}	_	V	C - 50-5	5 \/		5.1	7.5	1	8.5	ns
t _{PHL}	A	Y	C _L = 50pF	5V		5.1	7.5	1	8.5	ns
t _{PZH}	ŌĒ	V	C - 50=5	5)/		6.2	9.3	1	10.5	ns
t _{PZL}	OE	Υ	C _L = 50pF	5V		6.2	9.3	1	10.5	ns
t _{PHZ}	OF.	\ <u></u>	0 50.5	5)/		6.7	9.2	1	10.5	ns
t _{PLZ}	ŌĒ	Y	C _L = 50pF	5V		6.7	9.2	1	10.5	ns
t _{sk(o)}			C _L = 50pF	2V			2		2	ns
t _{sk(o)}			C _L = 50pF	3.3V			1.5		1.5	ns
t _{sk(o)}			C _L = 50pF	5V			1		1	ns

5.7 Noise Characteristics

VCC = 5V, CL = 50pF, TA = 25°C

PARAMETER	DESCRIPTION	MIN	TYP	MAX	UNIT
V _{OL(P)}	Quiet output, maximum dynamic V _{OL}				V
V _{OL(V)}	Quiet output, minimum dynamic V _{OL}				V
V _{OH(V)}	Quiet output, minimum dynamic V _{OH}				V
$V_{IH(D)}$	High-level dynamic input voltage	3.5			V
V _{IL(D)}	Low-level dynamic input voltage			1.5	V

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5.8 Typical Characteristics

T_A = 25°C (unless otherwise noted)

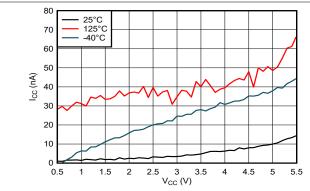


Figure 5-1. Supply Current Across Supply Voltage

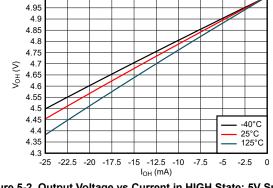


Figure 5-2. Output Voltage vs Current in HIGH State; 5V Supply

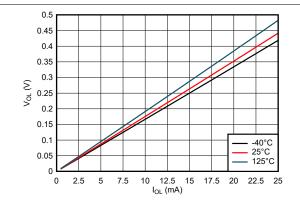


Figure 5-3. Output Voltage vs Current in LOW State; 5V Supply

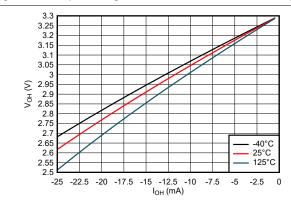


Figure 5-4. Output Voltage vs Current in HIGH State; 3.3V Supply

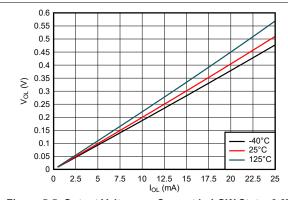


Figure 5-5. Output Voltage vs Current in LOW State; 3.3V Supply

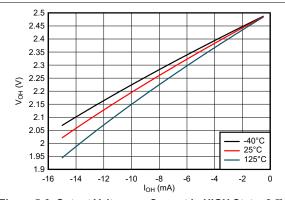
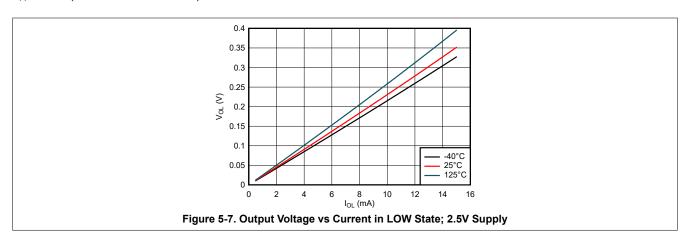


Figure 5-6. Output Voltage vs Current in HIGH State; 2.5V Supply



5.8 Typical Characteristics (continued)

T_A = 25°C (unless otherwise noted)

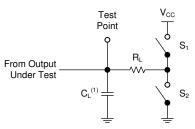


6 Parameter Measurement Information

Phase relationships between waveforms were chosen arbitrarily for the examples listed in the following table. All input pulses are supplied by generators having the following characteristics: $PRR \le 1MHz$, $Z_O = 50\Omega$, $t_t < 2.5ns$.

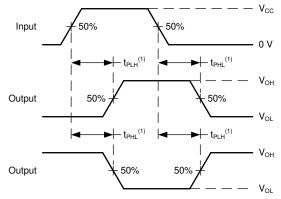
The outputs are measured individually with one input transition per measurement.

TEST	S1	S2	R _L	CL	ΔV	V _{cc}
t _{PLH} , t _{PHL}	OPEN	OPEN	_	15pF, 50pF	_	ALL
t _{PLZ} , t _{PZL}	CLOSED	OPEN	1kΩ	15pF, 50pF	0.15V	≤ 2.5V
t _{PHZ} , t _{PZH}	OPEN	CLOSED	1kΩ	15pF, 50pF	0.15V	≤ 2.5V
t _{PLZ} , t _{PZL}	CLOSED	OPEN	1kΩ	15pF, 50pF	0.3V	> 2.5V
t _{PHZ} , t _{PZH}	OPEN	CLOSED	1kΩ	15pF, 50pF	0.3V	> 2.5V



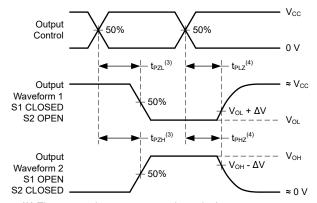
(1) C_L includes probe and test-fixture capacitance.

Figure 6-1. Load Circuit for 3-State Outputs



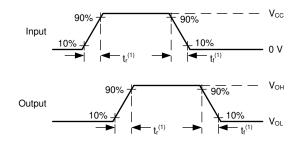
(1) The greater between t_{PLH} and t_{PHL} is the same as $t_{\text{pd}}.$

Figure 6-2. Voltage Waveforms Propagation Delays



- (3) The greater between $t_{\mbox{\scriptsize PZL}}$ and $t_{\mbox{\scriptsize PZH}}$ is the same as $t_{\mbox{\scriptsize en}}$.
- (4) The greater between $t_{\mbox{\scriptsize PLZ}}$ and $t_{\mbox{\scriptsize PHZ}}$ is the same as $t_{\mbox{\scriptsize dis}}.$

Figure 6-3. Voltage Waveforms Propagation Delays



(1) The greater between $t_{\rm r}$ and $t_{\rm f}$ is the same as $t_{\rm f}$.

Figure 6-4. Voltage Waveforms, Input and Output Transition Times

7 Detailed Description

7.1 Overview

The SN74AHC240-Q1 devices are organized as two 4-bit buffers/line drivers with separate output-enable (\overline{OE}) inputs. When \overline{OE} is low, the device passes data from the A inputs to the Y outputs. When \overline{OE} is high, the outputs are in the high-impedance state.

To place the device in the high-impedance state during power up or power down, tie \overline{OE} to V_{CC} through a pullup resistor; the current-sinking capability of the driver determines the minimum value of the resistor.

7.2 Functional Block Diagram

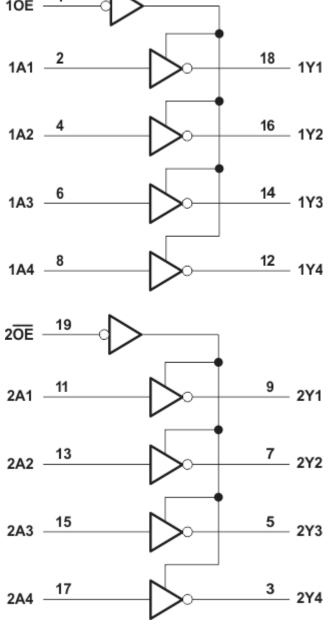


Figure 7-1. Logic Diagram (Positive Logic)

7.3 Feature Description

7.3.1 Balanced CMOS 3-State Outputs

This device includes balanced CMOS 3-state outputs. Driving high, driving low, and high impedance are the three states that these outputs can be in. The term *balanced* indicates that the device can sink and source similar currents. The drive capability of this device may create fast edges into light loads, so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device can drive larger currents than the device can sustain without being damaged. It is important for the output power of the device to be limited to avoid damage due to overcurrent. The electrical and thermal limits defined in the *Absolute Maximum Ratings* must be followed at all times.

When placed into the high-impedance state, the output will neither source nor sink current, with the exception of minor leakage current as defined in the *Electrical Characteristics* table. In the high-impedance state, the output voltage is not controlled by the device and is dependent on external factors. If no other drivers are connected to the node, then this is known as a floating node and the voltage is unknown. A pull-up or pull-down resistor can be connected to the output to provide a known voltage at the output while it is in the high-impedance state. The value of the resistor will depend on multiple factors, including parasitic capacitance and power consumption limitations. Typically, a $10k\Omega$ resistor can be used to meet these requirements.

Unused 3-state CMOS outputs should be left disconnected.

7.3.2 Standard CMOS Inputs

This device includes standard CMOS inputs. Standard CMOS inputs are high impedance and are typically modeled as a resistor in parallel with the input capacitance given in the *Electrical Characteristics*. The worst case resistance is calculated with the maximum input voltage, given in the *Absolute Maximum Ratings*, and the maximum input leakage current, given in the *Electrical Characteristics*, using Ohm's law $(R = V \div I)$.

Standard CMOS inputs require that input signals transition between valid logic states quickly, as defined by the input transition time or rate in the *Recommended Operating Conditions* table. Failing to meet this specification will result in excessive power consumption and could cause oscillations. More details can be found in *Implications of Slow or Floating CMOS Inputs*.

Do not leave standard CMOS inputs floating at any time during operation. Unused inputs must be terminated at V_{CC} or GND. If a system will not be actively driving an input at all times, then a pull-up or pull-down resistor can be added to provide a valid input voltage during these times. The resistor value will depend on multiple factors; a $10k\Omega$ resistor, however, is recommended and will typically meet all requirements.

7.3.3 Clamp Diode Structure

As Figure 7-2 shows, the outputs to this device have both positive and negative clamping diodes, and the inputs to this device have negative clamping diodes only.

CAUTION

Voltages beyond the values specified in the *Absolute Maximum Ratings* table can cause damage to the device. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.



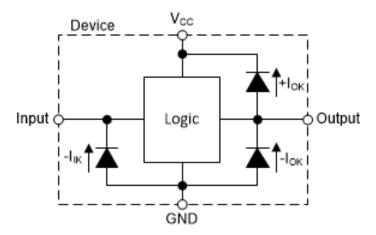


Figure 7-2. Electrical Placement of Clamping Diodes for Each Input and Output

7.4 Device Functional Modes

Table 7-1. Function Table (Each Buffer)

INPU	OUTPUT ⁽²⁾			
ŌE	A	Y		
L	Н	L		
L	L	Н		
Н	X	Z		

- (1) H = High Voltage Level, L = Low Voltage Level, X = Don't Care
- (2) H = Driving High, L = Driving Low, Z = High Impedance State

8 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

8.1 Application Information

The SN74AHC240-Q1 device is a high drive CMOS device that can be used for a multitude of bus-interface type applications where the data needs to be retained or latched. It can produce 24mA of drive current at 3.3V making it ideal for driving multiple outputs and also good for high-speed applications up to 100MHz. The inputs are 5.5V tolerant allowing it to translate down to V_{CC} .

8.2 Typical Application

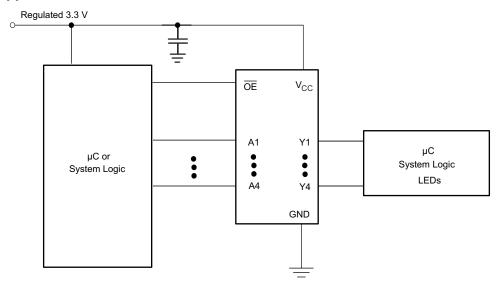


Figure 8-1. Typical Application Diagram

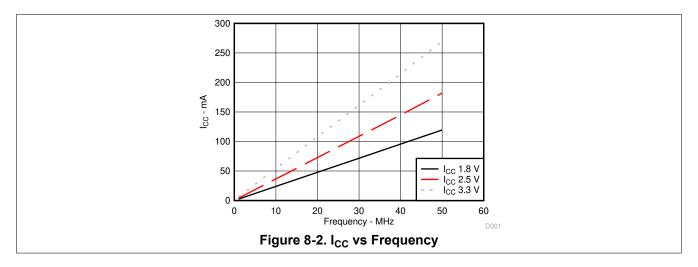
8.2.1 Design Requirements

This device uses CMOS technology and has balanced output drive. Take care to avoid bus contention because it can drive currents that would exceed maximum limits. The high drive will also create fast edges into light loads; therefore, routing and load conditions should be considered to prevent ringing.

8.2.2 Detailed Design Procedure

- 1. Recommended Input Conditions
 - Rise time and fall time specs: See (Δt/ΔV) in the Recommended Operating Conditions table.
 - Specified high and low levels: See (V_{IH} and V_{IL}) in the Recommended Operating Conditions table.
 - Inputs are overvoltage tolerant allowing them to go as high as 5.5V at any valid V_{CC}.
- 2. Recommend Output Conditions
 - Load currents should not exceed 25mA per output and 50mA total for the part.
 - Outputs should not be pulled above V_{CC}.

8.2.3 Application Curves



8.3 Power Supply Recommendations

The power supply can be any voltage between the min and max supply voltage rating located in Section 5.3.

Each V_{CC} terminal should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, TI recommends $0.1\mu F$ and if there are multiple V_{CC} terminals, then TI recommends $.01\mu F$ or $.022\mu F$ for each power terminal. It is okay to parallel multiple bypass capacitors to reject different frequencies of noise. A $0.1\mu F$ and $1\mu F$ are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results.

8.4 Layout

8.4.1 Layout Guidelines

When using multiple bit logic devices inputs should never float.

In many cases, functions or parts of functions of digital logic devices are unused (for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used). Such input pins should not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. The following rules specify what must be observed under all circumstances.

All unused inputs of digital logic devices must be connected to a high or low bias to prevent them from floating. The logic level that should be applied to any particular unused input depends on the function of the device. Generally they will be tied to GND or V_{CC} whichever makes more sense or is more convenient. It is generally okay to float outputs unless the part is a transceiver. If the transceiver has an output enable pin, then it will disable the outputs section of the part when asserted. This does not disable the input section of the IOs, so they cannot float when disabled.

8.4.2 Layout Example

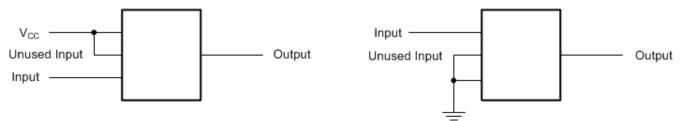


Figure 8-3. Layout Recommendation



9 Device and Documentation Support

9.1 Documentation Support

9.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, Implications of Slow or Floating CMOS Inputs
- Texas Instruments, Understanding Schmitt Triggers

9.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

9.3 Support Resources

TI E2E[™] support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

9.4 Trademarks

TI E2E[™] is a trademark of Texas Instruments.

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9.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

9.6 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.

10 Revision History

Changes from Revision * (March 2024) to Revision A (December 2024)

Page

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
PSN74AHC240QPWRQ1	ACTIVE	TSSOP	PW	20	2000	TBD	Call TI	Call TI	-40 to 125		Samples
SN74AHC240QPWRQ1	ACTIVE	TSSOP	PW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	AHC240Q	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE OPTION ADDENDUM

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OTHER QUALIFIED VERSIONS OF SN74AHC240-Q1:

● Catalog : SN74AHC240

• Military : SN54AHC240

NOTE: Qualified Version Definitions:

• Catalog - TI's standard catalog product

• Military - QML certified for Military and Defense Applications

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